

**IN THE CLAIMS**

Claims 1-24 (Canceled)

25. (Original) A manufacturing method of a resin-sealing type semiconductor device comprising the steps of:

preparing a multi-link lead frame formed by linking in a line with a plurality of package areas, each of the package areas including a plurality of inner leads, a thin sheet-shaped insulating member joined to an end portion of each of said inner leads and capable of supporting a semiconductor chip;

mounting said semiconductor chip on said insulating member in each of said package area;

connecting surface electrodes of said semiconductor chips and said inner leads corresponding thereto by a wire;

forming a seal portion by resin-sealing said semiconductor chips, said wire, and said insulating member; and

separating a plurality of outer leads exposed from said seal portion, from a frame section of said lead frame.

26. (Original) A manufacturing method of a resin-sealing type semiconductor device comprising the steps of:

preparing a matrix frame formed by arranging a plurality of package areas in a matrix arrangement, each of the package areas including a plurality of inner leads, a thin sheet-shaped insulating member joined to an end portion of each of said inner leads and capable of supporting a semiconductor chip;

mounting said semiconductor chip on said insulating member in each of said package area;

connecting surface electrodes of said semiconductor chips and said inner leads corresponding thereto by a wire;

forming a seal portion by resin-sealing said semiconductor chips, said wire, and said insulating member; and

separating a plurality of outer leads exposed from said seal portion, from a frame section of said matrix frame.

27. (Original) The manufacturing method of a semiconductor device according to claim 25, further comprising a step of mounting said semiconductor chip on a surface of an inner lead arrangement side of said insulating member when said semiconductor chip is mounted on said insulating member.

28. (Original) The manufacturing method of a semiconductor device according to claim 25,

wherein said semiconductor chip is arranged and mounted such that a length of a shorter side of a main surface of said semiconductor chip formed in an quadrilateral shape is twice or less than a distance from a tip of the inner leads arranged at the farthest location from a center line of the semiconductor chip in a plane direction, to said semiconductor chip, when said semiconductor chip is mounted on said insulating member.

29. (Original) The manufacturing method of a semiconductor device according to claim 25, further comprising a step of being assembled by using said lead frame in which said inner leads and said insulating member are joined by an adhesive layer disposed throughout the entire of a surface of an inner lead arrangement side of said insulating member.

30. (Original) The manufacturing method of a semiconductor device according to claim 25, further comprising a step of being assembled by using said lead frame in which said inner leads and said insulating member are joined by an adhesive layer disposed only on a lead joining portion of a surface of an inner lead arrangement side of said insulating member.